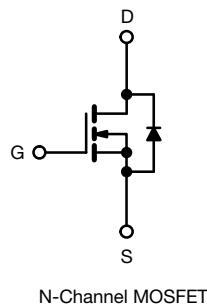
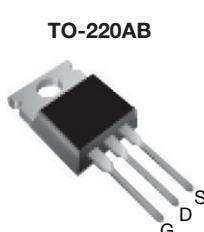


E Series Power MOSFET with Fast Body Diode

PRODUCT SUMMARY	
V_{DS} (V) at T_J max.	700
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10$ V 0.18
Q_g max. (nC)	106
Q_{gs} (nC)	14
Q_{gd} (nC)	33
Configuration	Single



ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free and Halogen-free	SiHP21N65EF-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current ($T_J = 150$ °C)	I_D	21	A
		13	
	I_{DM}	53	
Pulsed Drain Current ^a		1.7	W/°C
Linear Derating Factor	E_{AS}	367	mJ
Single Pulse Avalanche Energy ^b	P_D	208	W
Maximum Power Dissipation	T_J, T_{stg}	-55 to +150	°C
Operating Junction and Storage Temperature Range			
Drain-Source Voltage Slope	dV/dt	37	V/ns
Reverse Diode dV/dt ^d		31	
Soldering Recommendations (Peak Temperature) ^c	for 10 s	300	°C

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature.
- b. $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω, $I_{AS} = 5.1$ A.
- c. 1.6 mm from case.
- d. $I_{SD} \leq I_D$, $dI/dt = 100$ A/μs, starting $T_J = 25$ °C.

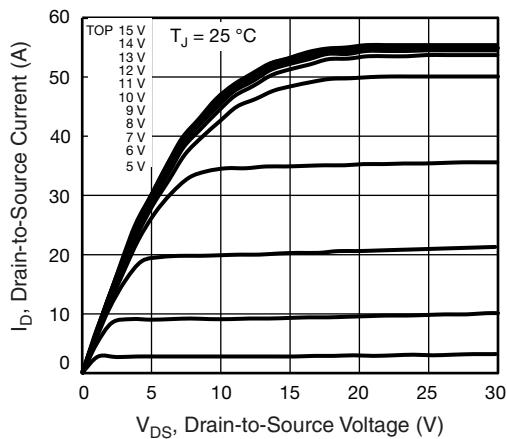
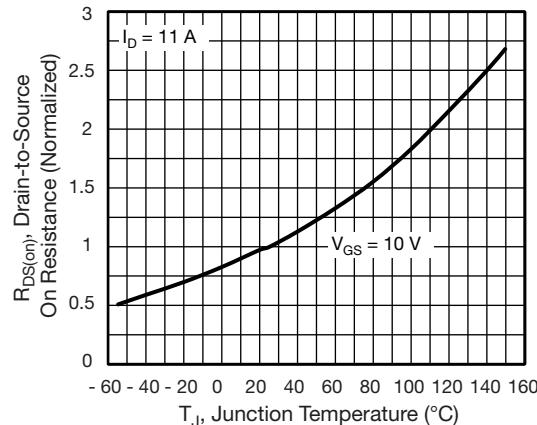
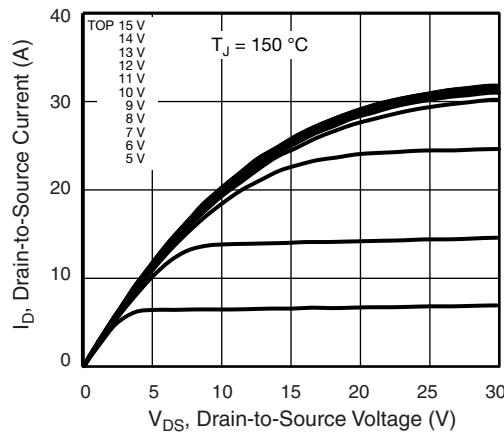
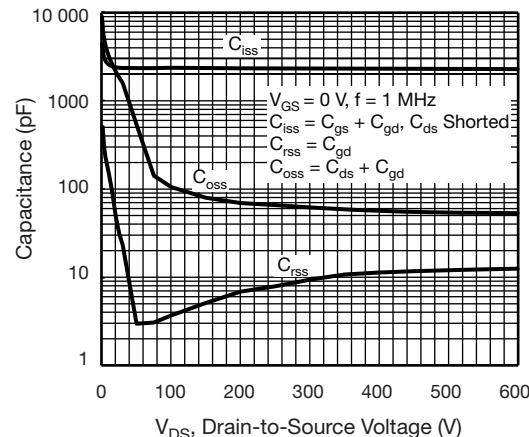
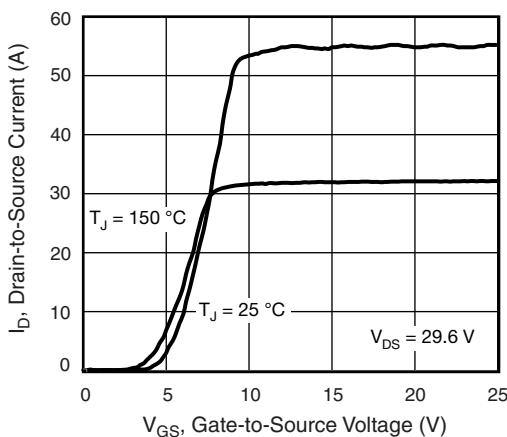
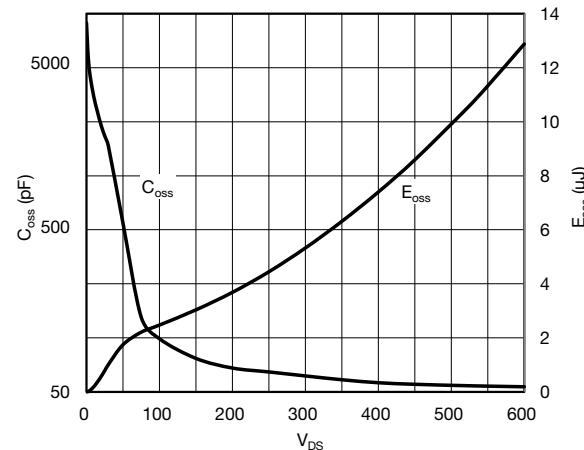


THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.5	°C/W

SPECIFICATIONS ($T_J = 25$ °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$ V, $I_D = 250$ μA		650	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, $I_D = 1$ mA		-	0.67	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250$ μA		2	-	4	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20$ V		-	-	± 100	nA
		$V_{GS} = \pm 30$ V		-	-	± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 520$ V, $V_{GS} = 0$ V		-	-	1	
		$V_{DS} = 520$ V, $V_{GS} = 0$ V, $T_J = 125$ °C		-	-	500	μA
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10$ V	$I_D = 11$ A	-	0.15	0.18	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 30$ V, $I_D = 11$ A		-	7.0	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0$ V, $V_{DS} = 100$ V, $f = 1$ MHz		-	2322	-	pF
Output Capacitance	C_{oss}			-	105	-	
Reverse Transfer Capacitance	C_{rss}			-	4	-	
Effective Output Capacitance, Energy Related ^a	$C_{o(er)}$	$V_{DS} = 0$ V to 520 V, $V_{GS} = 0$ V		-	84	-	
Effective Output Capacitance, Time Related ^b	$C_{o(tr)}$			-	293	-	
Total Gate Charge	Q_g			-	71	106	nC
Gate-Source Charge	Q_{gs}	$V_{GS} = 10$ V	$I_D = 11$ A, $V_{DS} = 520$ V	-	14	-	
Gate-Drain Charge	Q_{gd}			-	33	-	
Turn-On Delay Time	$t_{d(on)}$			-	22	44	ns
Rise Time	t_r	$V_{DD} = 520$ V, $I_D = 11$ A, $V_{GS} = 10$ V, $R_g = 9.1$ Ω		-	34	68	
Turn-Off Delay Time	$t_{d(off)}$		-	68	102		
Fall Time	t_f		-	42	84		
Gate Input Resistance	R_g	$f = 1$ MHz, open drain		-	0.78	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	21	A
Pulsed Diode Forward Current	I_{SM}			-	-	53	
Diode Forward Voltage	V_{SD}	$T_J = 25$ °C, $I_S = 11$ A, $V_{GS} = 0$ V		-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25$ °C, $I_F = I_S = 11$ A, $dl/dt = 100$ A/μs, $V_R = 25$ V		-	160	-	ns
Reverse Recovery Charge	Q_{rr}			-	1.2	-	μC
Reverse Recovery Current	I_{RRM}			-	14	-	A

Notes

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

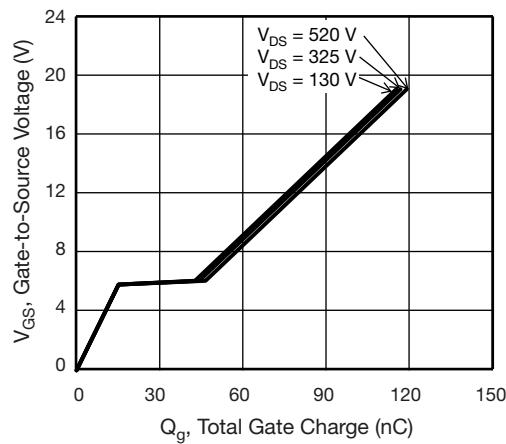


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

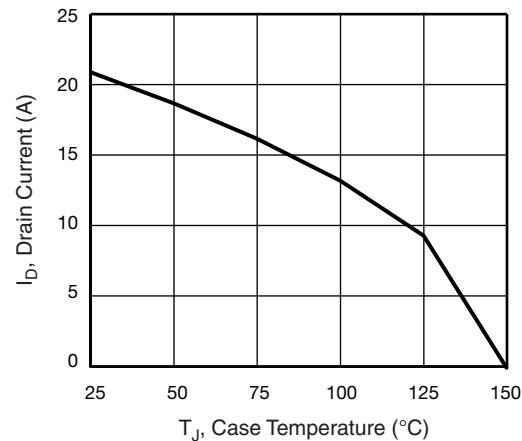


Fig. 10 - Maximum Drain Current vs. Case Temperature

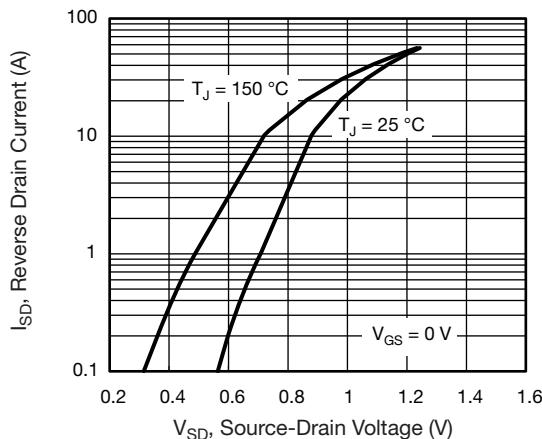


Fig. 8 - Typical Source-Drain Diode Forward Voltage

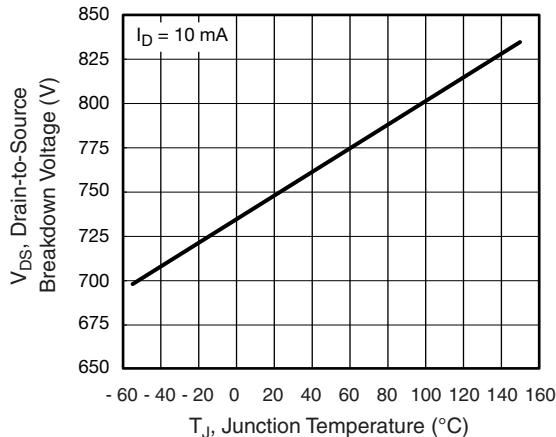


Fig. 11 - Temperature vs. Drain-to-Source Voltage

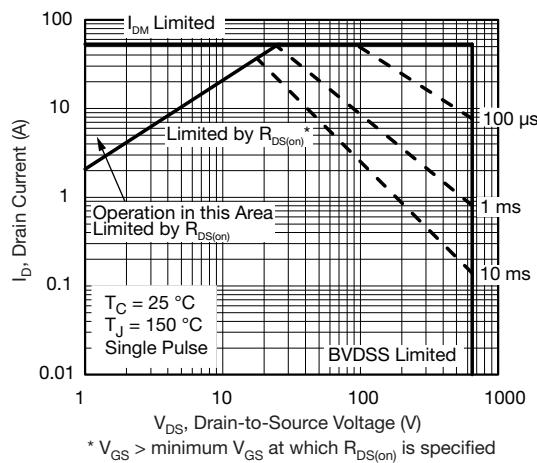


Fig. 9 - Maximum Safe Operating Area

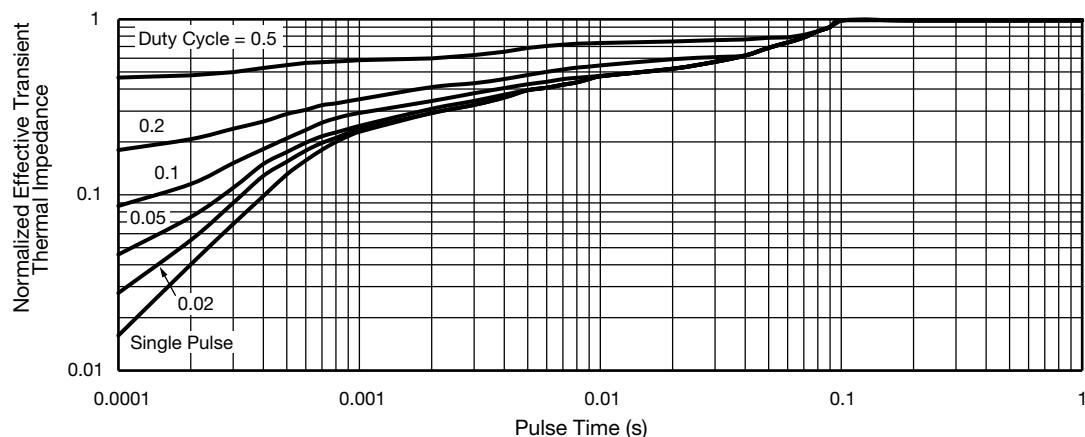


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

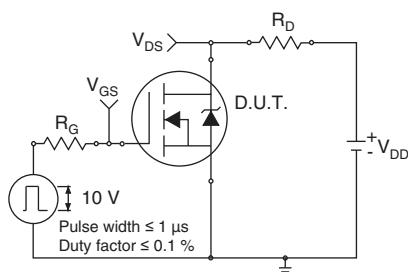


Fig. 13 - Switching Time Test Circuit

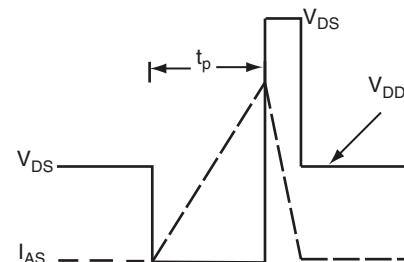


Fig. 16 - Unclamped Inductive Waveforms

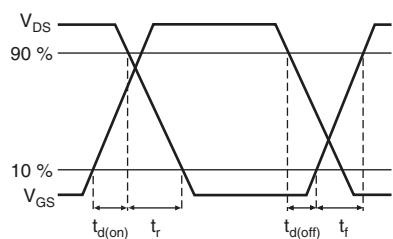


Fig. 14 - Switching Time Waveforms

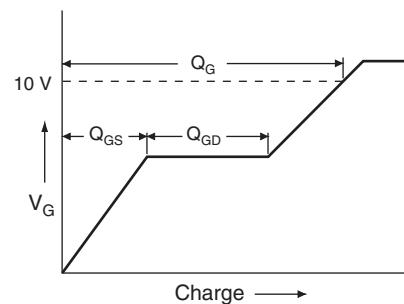


Fig. 17 - Basic Gate Charge Waveform

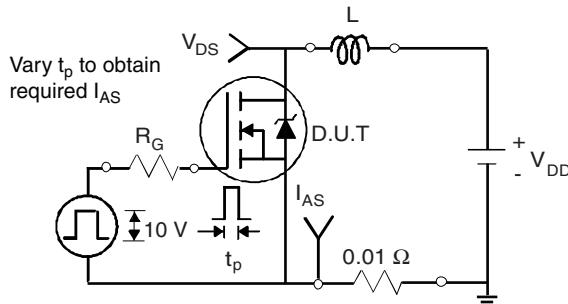


Fig. 15 - Unclamped Inductive Test Circuit

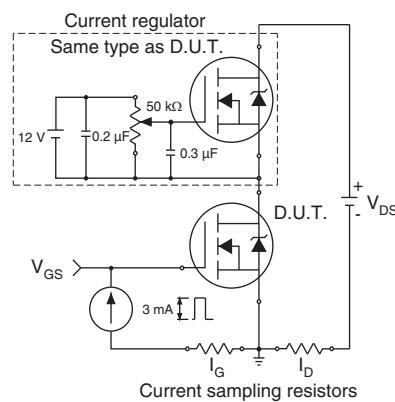
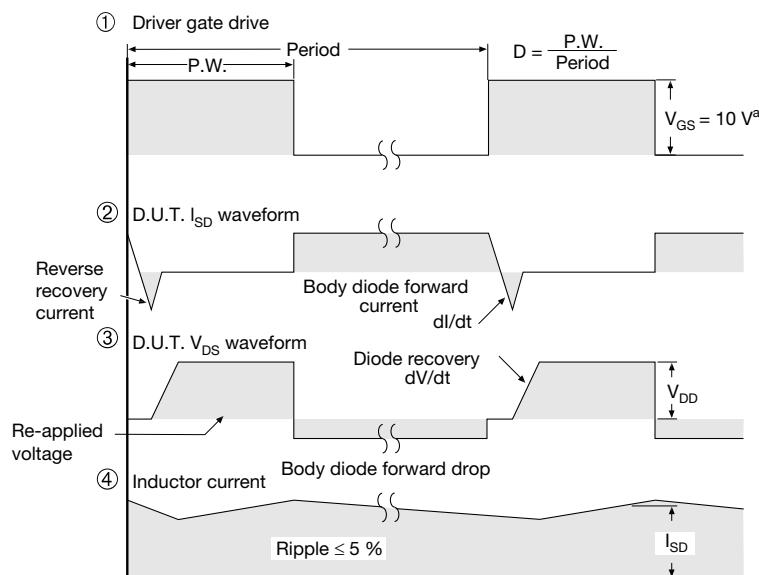
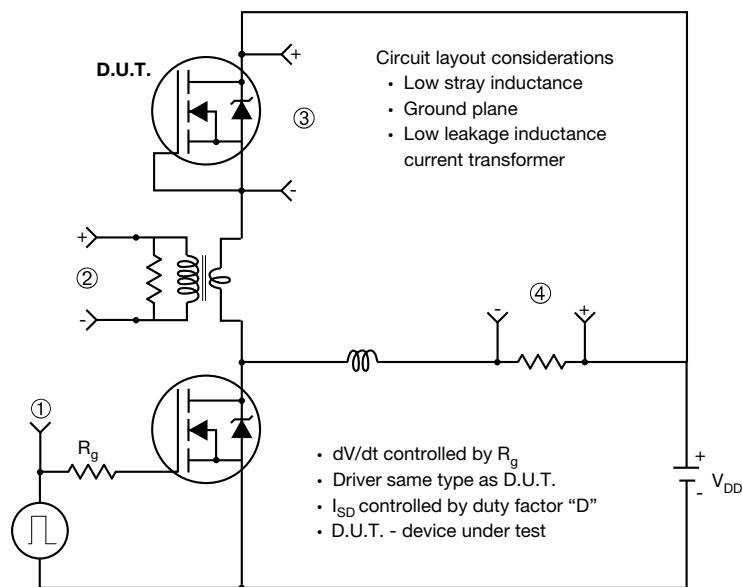
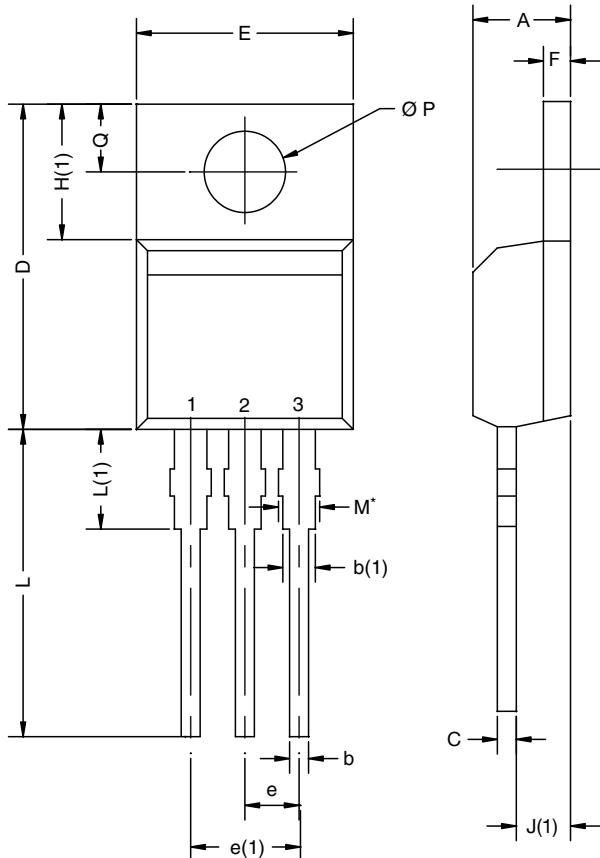


Fig. 18 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

Fig. 19 - For N-Channel

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TO-220AB

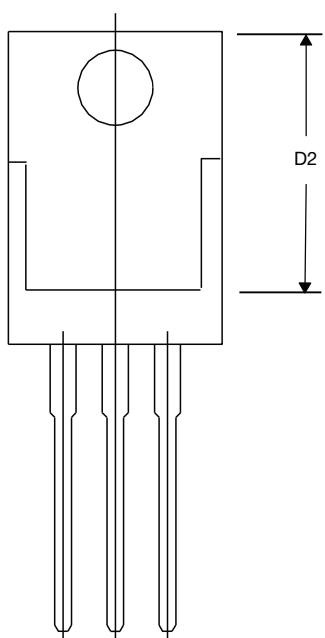


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: T14-0413-Rev. P, 16-Jun-14
DWG: 5471

Note

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM



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